

# RGTH40TS65

#### 650V 20A Field Stop Trench IGBT

V <sub>CES</sub>	650V
I <sub>C(100°C)</sub>	20A
V <sub>CE(sat) (Typ.)</sub>	1.6V
$P_D$	144W

#### ● Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

#### Applications

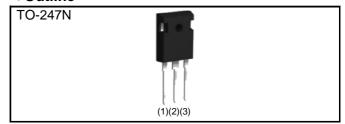
**PFC** 

**UPS** 

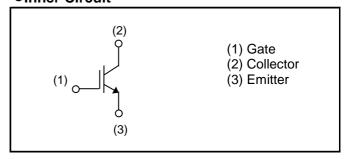
**Power Conditioner** 

ΙH

#### Outline



#### ●Inner Circuit



Packaging Specifications

	Packaging	Tube	
	Reel Size (mm)	-	
Type	Tape Width (mm)	-	
Type	Basic Ordering Unit (pcs)	450	
	Taping Code	C11	
	Marking	RGTH40TS65	

### ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V <sub>CES</sub>	650	V
Gate - Emitter Voltage		$V_{GES}$	±30	V
Collector Current	T <sub>C</sub> = 25°C	I <sub>C</sub>	40	А
	T <sub>C</sub> = 100°C	I <sub>C</sub>	20	А
Pulsed Collector Current		I <sub>CP</sub> *1	80	А
Power Dissipation	$T_C = 25^{\circ}C$	$P_{D}$	144	W
	T <sub>C</sub> = 100°C	$P_{D}$	72	W
Operating Junction Temperature		T <sub>j</sub>	-40 to +175	°C
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C

<sup>\*1</sup> Pulse width limited by T<sub>jmax.</sub>

#### ●Thermal Resistance

Parameter	Symbol	Values			Unit
raiametei		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	1.04	°C/W

## ullet IGBT Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
r ai ai nietei	Syllibol	Conditions	Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_C = 10 \mu A, V_{GE} = 0 V$	650	1	ı	V
Collector Cut - off Current	I <sub>CES</sub>	$V_{CE} = 650V, V_{GE} = 0V$	1	1	10	μΑ
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, V_{CE} = 0V$	1	1	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 13.3 \text{mA}$	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_C = 20A$ , $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.6 2.1	2.1	V

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Dorometer	Symbol	Conditions	Values			I Imit
Parameter			Min.	Тур.	Max.	Unit
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 30V	-	1060	-	
Output Capacitance	C <sub>oes</sub>	$V_{GE} = 0V$	-	47	-	pF
Reverse Transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	18	-	
Total Gate Charge	$Q_g$	V <sub>CE</sub> = 300V	-	40	-	
Gate - Emitter Charge	$Q_ge$	I <sub>C</sub> = 20A	-	9	-	nC
Gate - Collector Charge	$Q_{gc}$	V <sub>GE</sub> = 15V	-	15	-	
Turn - on Delay Time	t <sub>d(on)</sub>	$I_C = 20A, V_{CC} = 400V$	-	22	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	25	-	
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 25°C	-	73	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	48	-	
Turn - on Delay Time	t <sub>d(on)</sub>	$I_C = 20A, V_{CC} = 400V$	-	22	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	25	-	
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 175°C	-	83	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	58	-	
		$I_C = 80A, V_{CC} = 520V$		-	-	
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FULL SQUARE			-
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

Fig.1 Power Dissipation vs. Case Temperature

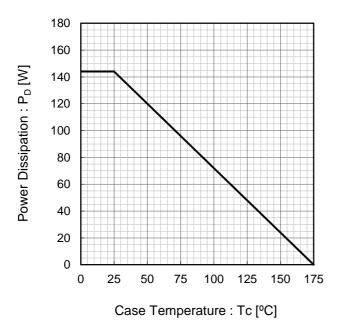


Fig.2 Collector Current vs. Case Temperature

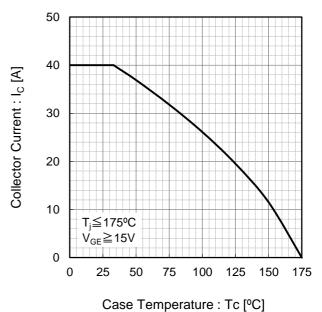
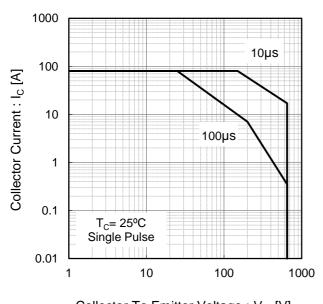
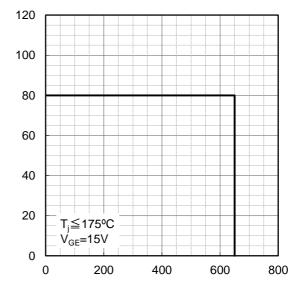


Fig.3 Forward Bias Safe Operating Area



Collector To Emitter Voltage :  $V_{CE}[V]$ 

Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage :  $V_{CE}[V]$ 

Collector Current : I<sub>C</sub> [A]

Fig.5 Typical Output Characteristics

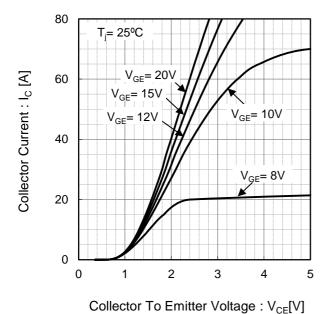
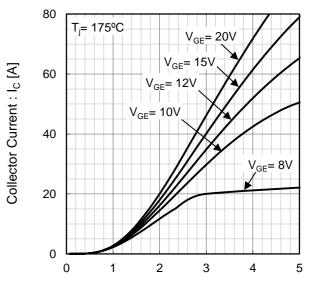


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : V<sub>CE</sub>[V]

Fig.7 Typical Transfer Characteristics

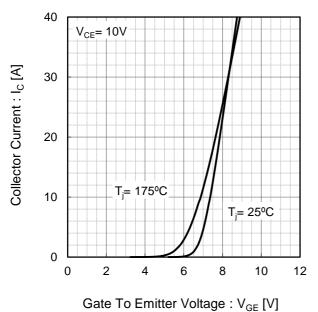
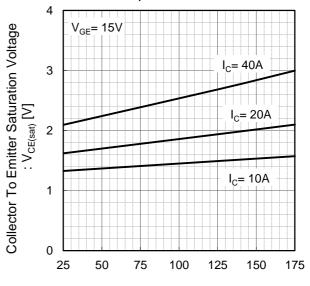


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T<sub>i</sub> [°C]

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

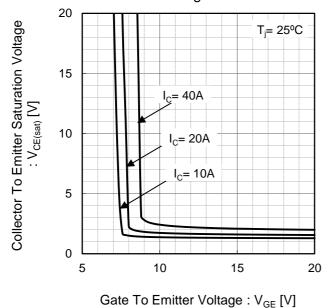
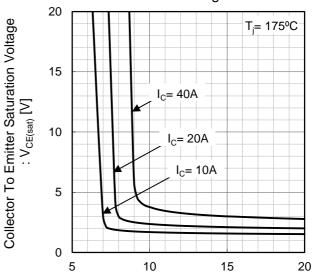


Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage: V<sub>GE</sub> [V]

Fig.11 Typical Switching Time vs. Collector Current

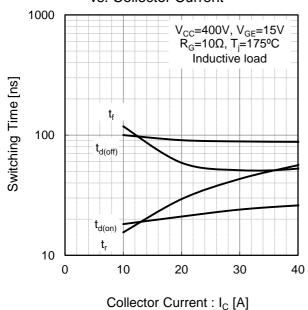
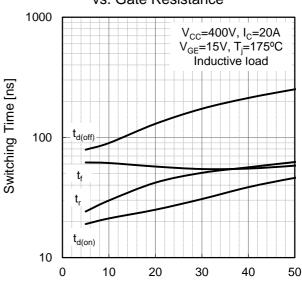


Fig.12 Typical Switching Time vs. Gate Resistance



Gate Resistance :  $R_G[\Omega]$ 

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1  $\mathsf{E}_{\mathsf{off}}$ 0.1 E<sub>on</sub>  $V_{CC}$ =400V,  $V_{GE}$ =15V  $R_{G}$ =10 $\Omega$ ,  $T_{i}$ =175°C Inductive load 0.01 0 10 20 30 40 Collector Current : I<sub>C</sub> [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ] 1  $\mathsf{E}_{\mathsf{off}}$  $E_{on}$ 0.1  $V_{CC}$ =400V,  $I_{C}$ =20A  $V_{GE}$ =15V,  $T_{j}$ =175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz  $V_{GE}=0V$ T;=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V<sub>CE</sub>[V]

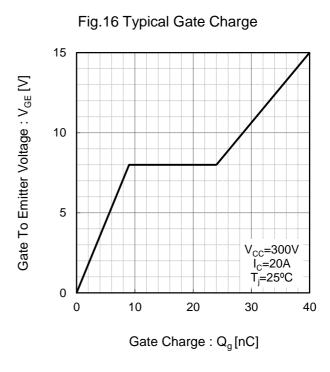
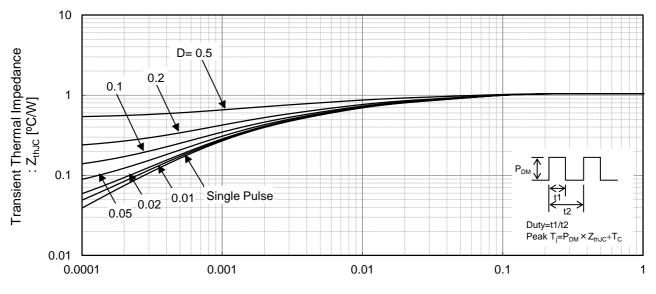


Fig.17 IGBT Transient Thermal Impedance



Pulse Width: t1[s]

### •Inductive Load Switching Circuit and Waveform

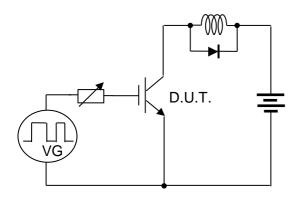


Fig.18 Inductive Load Circuit

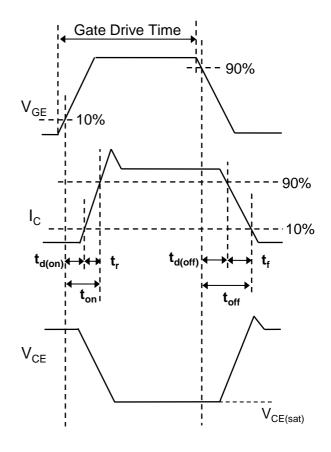


Fig.19 Inductive Load Waveform

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